

H11AA1, H11AA2, H11AA3, H11AA4
H11AA1X, H11AA2X, H11AA3X, H11AA4X



ISOCOM

COMPONENTS

A.C. INPUT PHOTOTRANSISTOR OPTICALLY COUPLED ISOLATORS



APPROVALS

- UL recognised, File No. E91231

'X' SPECIFICATION APPROVALS

- VDE 0884 in 3 available lead form :-
- STD
- G form
- SMD approved to CECC 00802

DESCRIPTION

The H11AA series of optically coupled isolators consist of two infrared light emitting diodes connected in inverse parallel and NPN silicon photo transistor in a standard 6 pin dual in line plastic package.

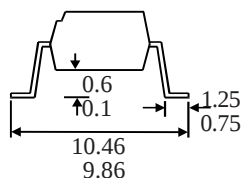
FEATURES

- Options :-
10mm lead spread - add G after part no.
Surface mount - add SM after part no.
Tape&reel - add SMT&R after part no.
- High Isolation Voltage ($5.3kV_{RMS}$, $7.5kV_{PK}$)
- AC or polarity insensitive input
- All electrical parameters 100% tested
- Custom electrical selections available

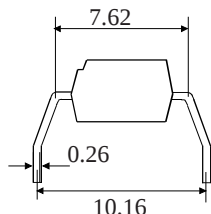
APPLICATIONS

- Computer terminals
- Industrial systems controllers
- Telephone sets, Telephone exchangers
- Signal transmission between systems of different potentials and impedances

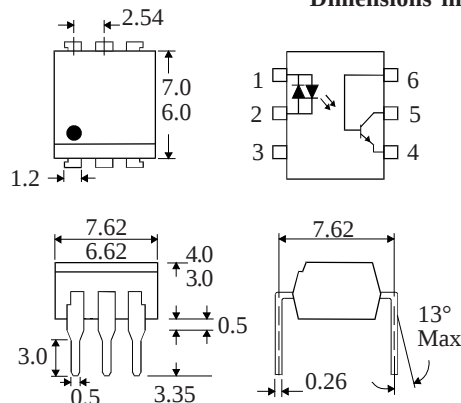
OPTION SM SURFACE MOUNT



OPTION G



Dimensions in mm



ABSOLUTE MAXIMUM RATINGS (25°C unless otherwise specified)

Storage Temperature _____ -55°C to +125°C
Operating Temperature _____ -30°C to +100°C
Lead Soldering Temperature
(1/16 inch (1.6mm) from case for 10 secs) 260°C

INPUT DIODE

Forward Current _____ $\pm 50mA$
Power Dissipation _____ 70mW

OUTPUT TRANSISTOR

Collector-emitter Voltage BV_{CEO} _____ 35V
Collector-base Voltage BV_{CBO} _____ 35V
Emitter-collector Voltage BV_{ECO} _____ 6V
Emitter-base Voltage BV_{EBO} _____ 6V
Collector Current _____ 50mA
Power Dissipation _____ 150mW

POWER DISSIPATION

Total Power Dissipation _____ 200mW
(derate linearly 4.67mW/°C above 25°C)

ISOCOM COMPONENTS LTD

Unit 25B, Park View Road West,
Park View Industrial Estate, Brenda Road
Hartlepool, TS25 1UD England Tel: (01429)863609
Fax: (01429)863581 e-mail sales@isocom.co.uk
<http://www.isocom.com>

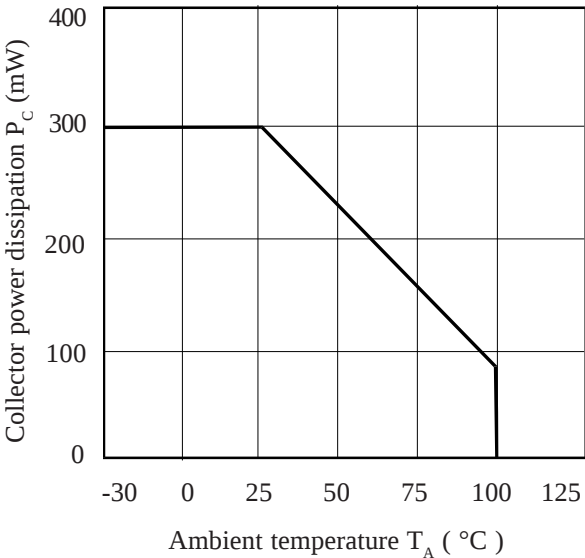
ELECTRICAL CHARACTERISTICS ($T_A = 25^\circ\text{C}$ Unless otherwise noted)

PARAMETER		MIN	TYP	MAX	UNITS	TEST CONDITION
Input	Forward Voltage (V_F)		1.2	1.5	V	$I_F = \pm 10\text{mA}$
Output	Collector-emitter Breakdown (BV_{CEO}) (note 2)	35			V	$I_C = 0.1\text{mA}$
	Collector-base Breakdown (BV_{CBO})	35			V	$I_C = 100\mu\text{A}$
	Emitter-base Breakdown (BV_{EBO})	6			V	$I_E = 100\mu\text{A}$
	Emitter-collector Breakdown (BV_{ECO})	6			V	$I_E = 10\mu\text{A}$
	Collector-emitter Dark Current (I_{CEO})			100	nA	$V_{CE} = 20\text{V}$
Coupled	Current Transfer Ratio (CTR) (note 2)					
	H11AA4	100			%	$\pm 10\text{mA } I_F, 10\text{V } V_{CE}$
	H11AA3	50			%	$\pm 10\text{mA } I_F, 10\text{V } V_{CE}$
	H11AA1	20			%	$\pm 10\text{mA } I_F, 10\text{V } V_{CE}$
	H11AA2	10			%	$\pm 10\text{mA } I_F, 10\text{V } V_{CE}$
	Collector-emitter Saturation Voltage $V_{CE(SAT)}$			0.4	V	$\pm 10\text{mA } I_F, 0.5\text{mA } I_C$
	Input to Output Isolation Voltage V_{ISO}	5300			V_{RMS}	See note 1
		7500			V_{PK}	See note 1
	Input-output Isolation Resistance R_{ISO}	5×10^{10}			Ω	$V_{IO} = 500\text{V}$ (note 1)
	Rise Time, tr		4		μS	$V_{CE} = 2\text{V}, I_C = 2\text{mA}$
	Fall Time, tf		3		μS	$R_L = 100\Omega$

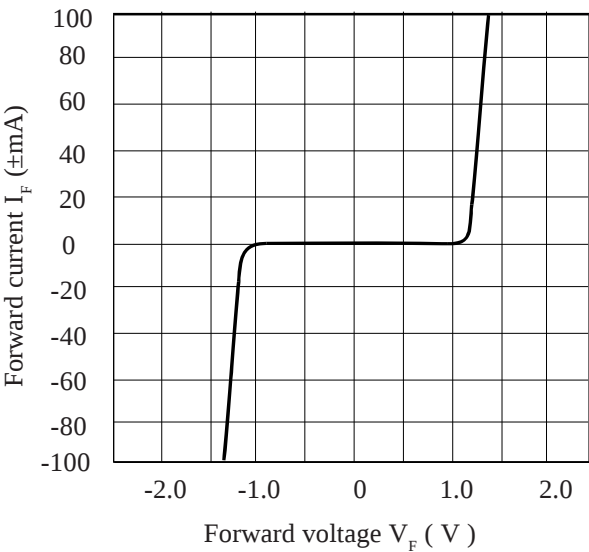
Note 1 Measured with input leads shorted together and output leads shorted together.

Note 2 Special Selections are available on request. Please consult the factory.

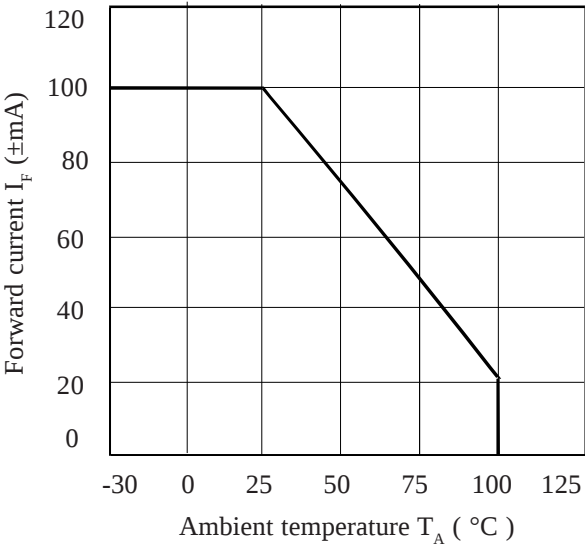
Collector Power Dissipation vs. Ambient Temperature



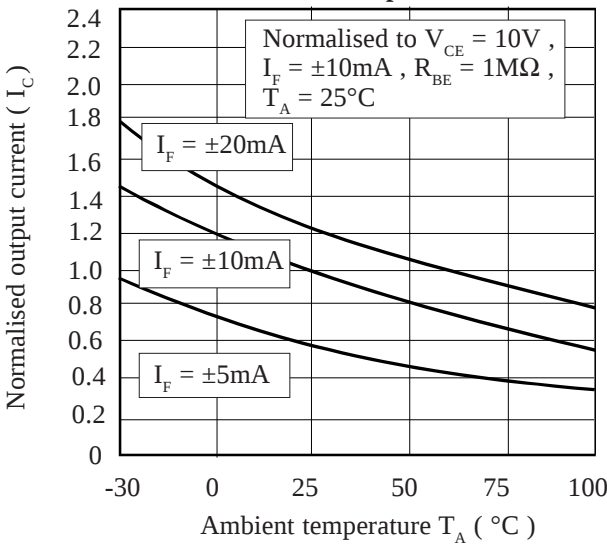
Forward Current vs. Forward Voltage



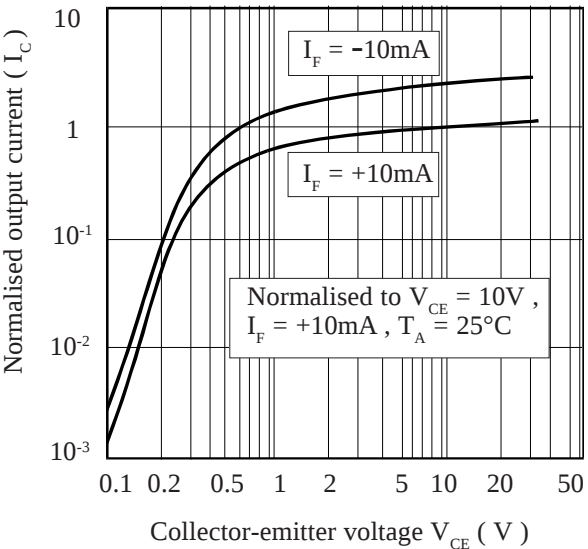
Forward Current vs. Ambient Temperature



Normalised Output Current vs. Ambient Temperature



Normalised Output Current vs. Collector-emitter Voltage



Normalised Output Current vs. Forward Current

